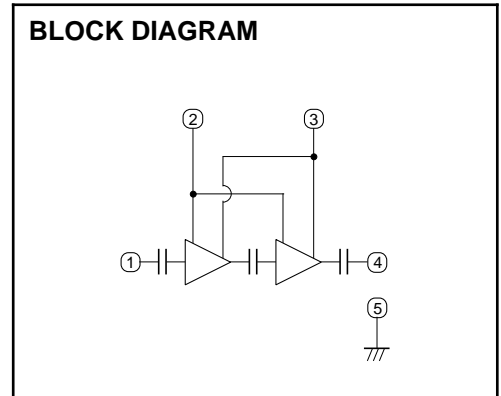
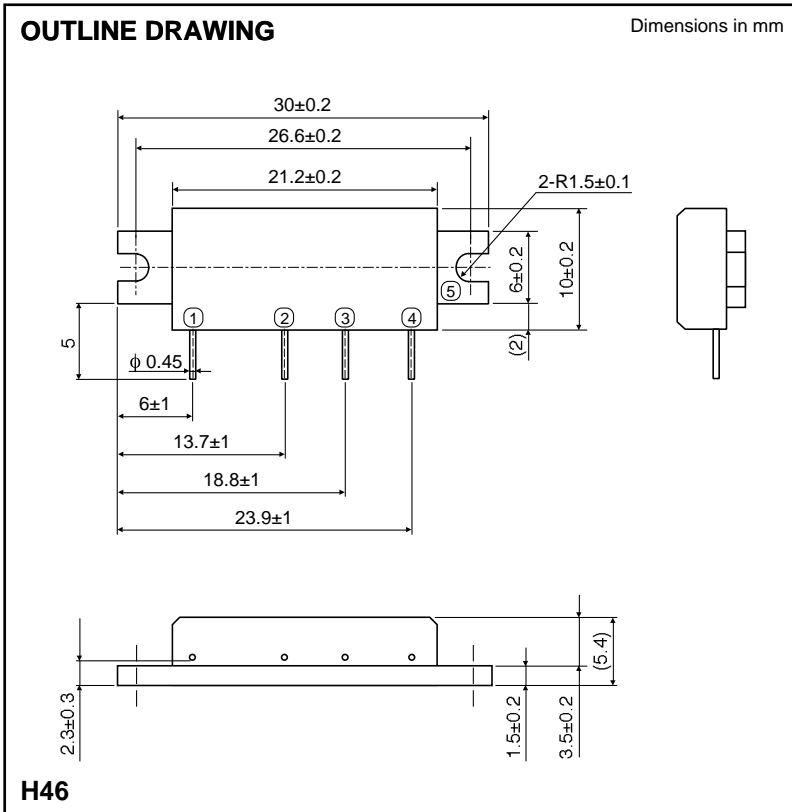


MITSUBISHI RF POWER MODULE
M68757L

SILICON MOS FET POWER AMPLIFIER, 806-870MHz, 3W, FM PORTABLE RADIO



- PIN:
 ①Pin : RF INPUT
 ②V_{GG} : GATE BIAS SUPPLY
 ③V_{DD} : DRAIN BIAS SUPPLY
 ④P_O : RF OUTPUT
 ⑤GND: FIN

ABSOLUTE MAXIMUM RATINGS (T_c=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
V _{DD}	Supply voltage	V _{GG} 3.5V, Z _G =Z _L =50	9.2	V
V _{GG}	Gate bias voltage		4	V
P _{in}	Input power	f=806-870MHz, Z _G =Z _L =50	70	mW
P _O	Output power	f=806-870MHz, Z _G =Z _L =50	5	W
T _{C (OP)}	Operation case temperature	f=806-870MHz, Z _G =Z _L =50	-30 to +100	°C
T _{stg}	Storage temperature		-40 to +100	°C

Note. Above parameters are guaranteed independently.

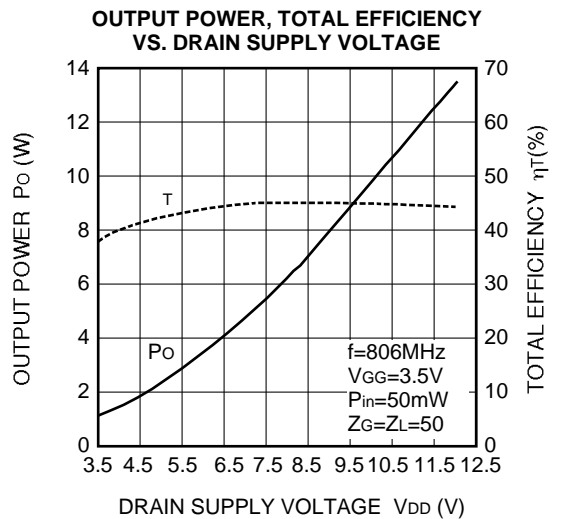
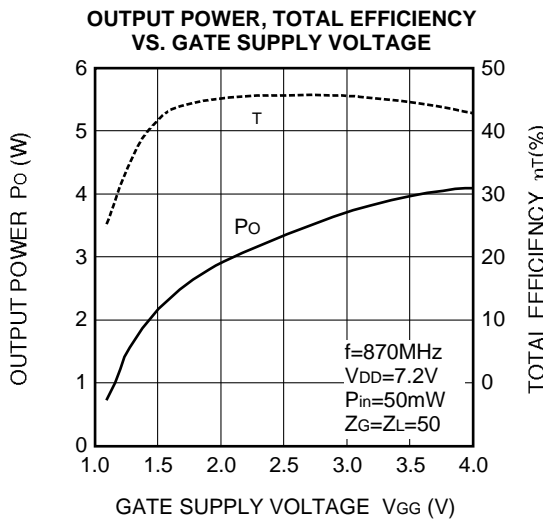
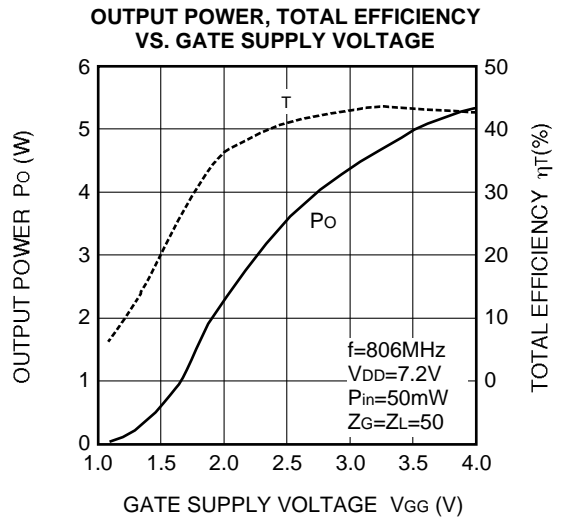
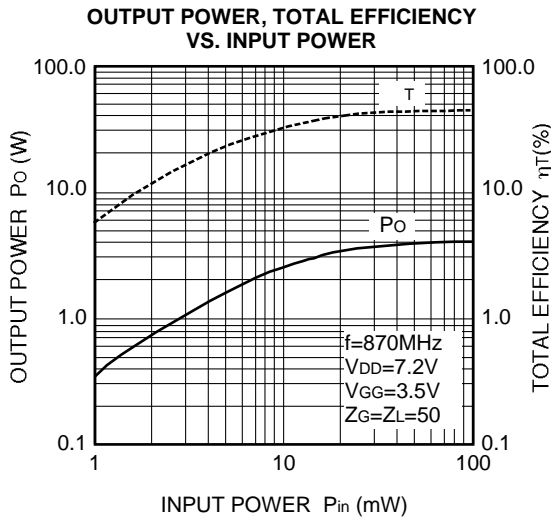
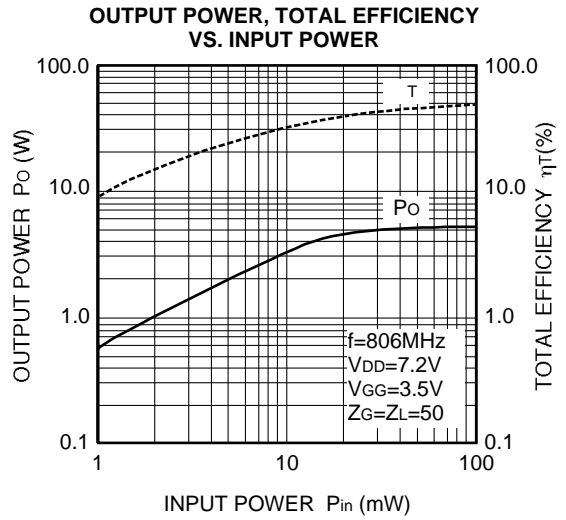
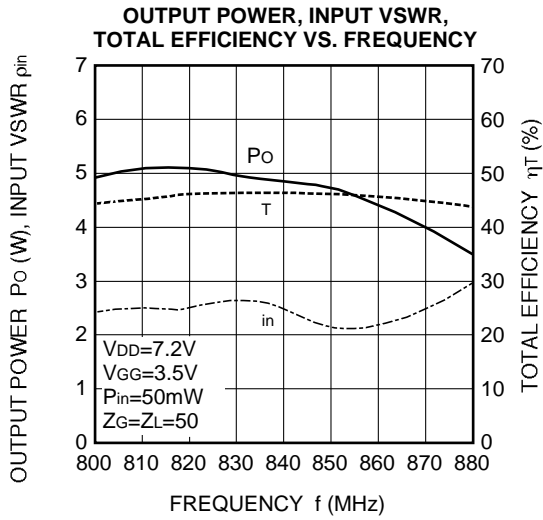
ELECTRICAL CHARACTERISTICS (T_c=25°C, Z_G=Z_L=50 unless otherwise noted)

Symbol	Parameter	Test conditions	Limits		Unit
			Min	Max	
f	Frequency range		806	870	MHz
P _O	Output power		3		W
η	Total efficiency	V _{DD} =7.2V, V _{GG} =3.5V, P _{in} =50mW	30		%
2f _o	2nd. harmonic			-28	dBc
in	Input VSWR			4	—
—	Stability	Z _G =Z _L =50, V _{DD} =5-9.2V, Load VSWR <4:1	No parasitic oscillation		—
—	Load VSWR tolerance	V _{DD} =9V, P _{in} =50mW, P _O =3W (V _{GG} Adjust), Z _L =20:1	No degradation or destroy		—

Note. Above parameters, ratings, limits and test conditions are subject to change.

SILICON MOS FET POWER AMPLIFIER, 806-870MHz, 3W, FM PORTABLE RADIO

TYPICAL PERFORMANCE DATA



SILICON MOS FET POWER AMPLIFIER, 806-870MHz, 3W, FM PORTABLE RADIO

